Magnetic and crystal structures of the polymorphic Pr₅Si₂Ge₂ compound

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(Received 25 April 2007; revised manuscript received 18 June 2007; published 21 August 2007)

Crystallographic and magnetic structures of the polymorphisms of Pr₅Si₂Ge₂ compound: the tetragonal t-Pr₅Si₂Ge₂ and the monoclinic *m*-Pr₅Si₂Ge₂, are investigated by neutron powder diffraction at different temperatures. The t-Pr₅Si₂Ge₂ crystallizes in the Zr_5Si_4 -type structure with the space group $P4_12_12$ down to 4 K. Long-range magnetic ordering takes place at $T_c=52$ K, and the magnetic structure can be modeled with the magnetic space group $P4_12_1'2'$. The net magnetic moment occurs exclusively along the c direction. The lattice parameters change continuously around T_C with a small negative magnetovolume effect, indicating a secondorder phase transition. The m-Pr₅Si₂Ge₂ crystallizes in the Gd₅Si₂Ge₂-type structure with the space group $P112_1/a$ down to 4 K. Long-range magnetic ordering occurs at $T_c=40$ K and the magnetic structure can be modeled with the magnetic space group $P112_1'/a'$. The net magnetic moment lies on the *ab* plane, with the main component along the a axis. No other magnetic transition is observed below T_C for both the compounds, and the largest shrinking of lattice parameter upon cooling through T_C occurs along the direction with the largest net magnetic moment component. The relatively stable existence at room temperature of the polymorphic $Pr_5Si_2Ge_2$ is readily understood based on the correlation between the crystal structures of $t-Pr_5Si_2Ge_2$ and m-Pr₅Si₂Ge₂. In the scenario of the Ruderman-Kittel-Kasuya-Yosida interaction model, the complex noncollinear magnetic structures of the compounds can be attributed to a competition of different Pr-Pr exchange interactions due to the different chemical environments around Pr atoms on different sites and to the broad range of the Pr-Pr distances.

DOI: 10.1103/PhysRevB.76.064425

PACS number(s): 75.25.+z, 75.30.Kz, 75.30.Sg

I. INTRODUCTION

The discovery of giant magnetocaloric effect (MCE) in Gd₅Si₂Ge₂ by Pecharsky and Gschneidner¹ has renewed the interest in recent years in the family of intermetallic compounds $R_5(Si_xGe_{1-x})_4$ (*R*=rare earth metal), which were known and studied 40 years ago.² The incidence of the MCE in Gd₅Si₂Ge₂ is closely related to a simultaneous occurrence of the first-order magnetic and martensiticlike structural phase transitions.^{3,4} The strong coupling of magnetic and crystallographic sublattices is also responsible for the strong magnetoelastic effect^{3,5} and the giant magnetoresistance⁶ in $Gd_5(Si_xGe_{1-x})_4$. Knowledge of magnetic and crystallographic structures of these compounds is obviously indispensable for understanding the microscopic physical mechanisms controlling the observed intriguing behavior. The magnetic structure of Gd₅Ge₄ was recently elucidated from x-ray resonant magnetic scattering data,⁷ yet the determination of the magnetic structures of $Gd_5(Si_xGe_{1-x})_4$ by neutron diffraction remains a challenge due to the huge neutron absorption cross section of the majority Gd isotope. Therefore, the magnetic structures of many binary and pseudobinary compounds $R_5(Si_xGe_{1-x})_4$ other than R=Gd have been extensively visited or revisited recently.^{8–15} In the study of $Tb_5(Si_{1-x}Ge_x)_4$ system, Ritter *et* al. found that Tb₅Si₂Ge₂ crystallized in monoclinic paramagnetic $Gd_5Si_2Ge_2$ -type structure (space $P112_1/a$) at room temperature and in the orthorhombic ferromagnetic Gd₅Si₄-type structure (space group *Pnma*) at low temperature.¹⁰ In contrast to the Gd₅Si₂Ge₂, however, the paramagnetic monoclinic Tb₅Si₂Ge₂ first transformed to a monoclinic ferromagnetic structure (T_C =110 K) before the further transition to the orthorhombic ferromagnetic Gd_5Si_4 -type structure ($T_t = 100$ K) on cooling, indicating that the structural and magnetic transitions are not fully coupled in $Tb_5Si_2Ge_2$.¹¹ The monoclinic ferromagnetic structure was also stable down to 4 K in Nd₅Si_{1.45}Ge_{2.55} and Pr₅Si_{1.5}Ge_{2.5} (Ref. 12) and in $Er_5(Si_xGe_{1-x})_4$.¹⁵ In particular, Er_5Si_4 crystallized in the Gd_5Si_4 -type structure at room temperature and underwent a structural transition to the lower symmetry monoclinic structure (Gd₅Si₂Ge₂-type, *P*112₁/*a*) upon cooling in the temperature range between 160 and 220 K, whereas magnetic ordering developed below the structural transition temperature (T_C =30 K) and the crystallographic structure retained the monoclinic symmetry.^{15,16}

Another intriguing feature of $Gd_5(Si_xGe_{1-x})_4$ is the polymorphic behavior in paramagnetic state around x=0.5. Monoclinic Gd₅Si₂Ge₂ underwent an elastic transformation to high temperature Gd₅Si₄-type structure in the temperature range of 573-593 K upon heating, which was reversible during heating and slow cooling but irreversible during rapid cooling.¹⁷ However, the transformation of monoclinic Gd₅Si_{2.09}Ge_{1.91} to high temperature Gd₅Si₄-type structure became sluggish, incomplete and irreversible between room temperature and 730 K.¹⁸ It is noteworthy that the lower symmetry monoclinic Gd₅Si_{2.09}Ge_{1.91} was prepared by heattreating the as-arc melted counterpart, which crystallized in the higher symmetry orthorhombic Gd₅Si₄-type structure, at 1570 K for 7 h followed by a fairly rapid cooling to room temperature and the resulting alloy contained ~ 14 vol % of the orthorhombic phase. The magnetization curves of the asarc-melted and heat-treated samples at 10 kOe (*M*-*T* curves) showed little difference, except that the Curie temperature of

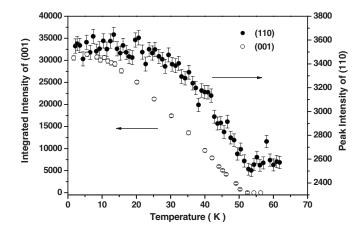


FIG. 1. Temperature dependence of the integrated intensity of (001) peak and the peak intensity of (110) reflection of t-Pr₅Si₂Ge₂ on warming, measured by high-flux BT-7 spectrometer at NIST-NCNR.

the monoclinic phase was about 5 K lower than that of the orthorhombic phase. The monoclinic phase exhibited the first-order magnetic-martensiticlike structural transitions around T_C (~295 K), whereas the orthorhombic phase showed exclusively the normal second-order paramagnetic-ferromagnetic transition at T_C (~300 K).¹⁸

Polymorphism was also observed in Pr₅Si₂Ge₂, but the features of the structural transition and the structure dependence of physical properties were distinguished from those of $Gd_5Si_2Ge_2$.¹⁹ In the study of $Pr_5(Si_xGe_{1-x})_4$ system, Yang et al. found that the as-arc-melted Pr₅Si₂Ge₂ crystallized in the monoclinic $Gd_5Si_2Ge_2$ -type structure (*m*-Pr₅Si₂Ge₂, $P112_1/a$) at room temperature with a minor tetragonal phase $(\sim 3 \text{ wt }\%)$ and the high purity single-phase tetragonal $Pr_5Si_2Ge_2$ (*t*- $Pr_5Si_2Ge_2$) could be fabricated by annealing the as-arc-melted *m*-Pr₅Si₂Ge₂ at 1273 K followed by a water quench. The *t*-Pr₅Si₂Ge₂ crystallized in the Zr₅Si₄-type structure (space group $P4_12_12$), which is taken by many light rare earth silicides (R_5Si_4) . X-ray powder diffraction (XRD) showed that annealing the samples at 873 K for two months did not result in noticeable change of the XRD patterns for both the m-Pr₅Si₂Ge₂ and the t-Pr₅Si₂Ge₂, indicating their relatively stable character at room temperature. The magnetization and electronic transport properties of these two compounds exhibited similar behavior, but their magnetic ordering temperatures differed by more than 10 K. At 5 K and 50 kOe, both compounds manifested a magnetic moment per Pr atom much lower than the saturation value of a free Pr³⁺ ion $(3.5\mu_B)$, possibly implying complex noncollinear magnetic structures at low temperature, although the effects due to the presence of crystalline electric field (CEF) and large magnetocrystalline anisotropy cannot be ruled out. In the present work, the crystallographic and magnetic structures of the polymorphic $Pr_5Si_2Ge_2$ (*m*- and *t*- $Pr_5Si_2Ge_2$) in the temperature range between 4 and 300 K are studied by means of neutron powder diffraction. After a brief description of experiments in Sec. II, the refinement results of the crystal and magnetic structures at different temperatures are presented in Sec. III. A discussion on the magnetic structures and the correlation between the crystal structures of the *m*- and t-Pr₅Si₂Ge₂ is given in Sec. IV, and a summary of the work in Sec. V.

II. EXPERIMENT

Details of the preparation of alloy samples have been described in Ref. 19. Polycrystalline Pr₅Si₂Ge₂ alloy was prepared by arc melting the corresponding mixtures of pure metal components (with purity better than 99.9% for Pr and 99.9999% for Si and Ge) in a water-cooled copper hearth under an argon atmosphere. The alloy was arc melted 4-5 times, with the alloy button being turned over after each melting to improve the homogeneity of the alloy. Part of the as-arc-melted alloy was sealed in an evacuated quartz tube and annealed at 1273 K for one week, followed by a water quench. The chemical compositions of both the as-arcmelted and the heat-treated samples were determined to be in good agreement with the nominal compositions by means of an inductively coupled plasma atomic emission spectroscopy (TJACo.). XRD (Rigaku D/max 2500, Cu $K\alpha$ radiation, $50 \text{ kV} \times 250 \text{ mA}$) showed that the as-arc-melted sample crystallized in the monoclinic Gd₅Si₂Ge₂-type structure $(P112_1/a)$ and the heat-treated sample in the tetragonal Zr_5Si_4 -type structure ($P4_12_12$). The as-arc-melted and the heat-treated samples are referred hereafter as *m*-Pr₅Si₂Ge₂ and *t*-Pr₅Si₂Ge₂, respectively.

Neutron powder diffraction (NPD) experiments in the temperature range between 4 and 300 K were performed at the NIST Center for Neutron Research (NCNR). The magnetic ordering was first examined on the high-flux BT-7 spec-

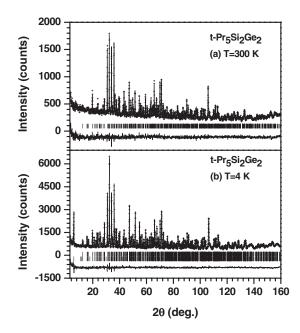


FIG. 2. Experimental (crosses) and calculated (solid line) intensities of t-Pr₅Si₂Ge₂ at (a) 300 K and (b) 4 K. Differences between the experimental and calculated patterns are shown at the bottom of the figure. The vertical bars indicate the expected nuclear reflection positions. The expected magnetic reflection positions are marked by the bars on the lower row in (b).

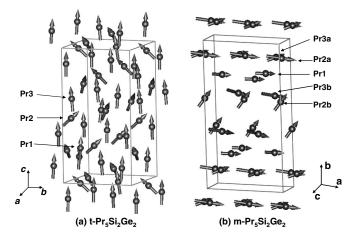


FIG. 3. The magnetic structure of (a) t-Pr₅Si₂Ge₂ and (b) m-Pr₅Si₂Ge₂. Only the magnetic atoms are shown.

trometer with a neutron wavelength of 2.4649 Å provided by a pyrolytic graphite monochromator and filter. The NPD data for refinements of the crystallographic and magnetic structures were collected on the high-resolution, 32-counter BT-1 diffractometer. Monochromatic neutron beam of wavelength 1.5403(1) Å was used for the *t*-Pr₅Si₂Ge₂ and a wavelength of 2.0787 Å for the *m*-Pr₅Si₂Ge₂. The NPD data were collected in the 2θ range of 3°–168° with a step of 0.05°. The program FULLPROF (Ref. 20) was used for the Rietveld refinement of the crystallographic and magnetic structures of the compounds.

III. RESULTS

A. Crystal and magnetic structures of *t*-Pr₅Si₂Ge₂

Neutron powder diffraction at room temperature confirms that the investigated sample is single phase and crystallizes in the tetragonal Zr_5Si_4 -type structure. The NPD pattern can be well indexed by the space group $P4_12_12$. On cooling the sample, the (001) peak develops around $2\theta = 6^{\circ}$, which is forbidden by the space group $P4_12_12$ and is attributed to a purely magnetic contribution. In the temperature range between 4 and 300 K, no reflection with fractional index is observed, suggesting the same unit cell for the crystallographic and magnetic structures. Figure 1 shows the evolutions of the integrated intensity of the (001) peak and the peak intensity of the (110) reflection on warming, and both indicate that the long-range magnetic ordering disappears around $T_C = 52$ K, in good coincidence with the magnetization measurements (T_C =50 K).¹⁹ No other magnetic transition occurs below T_C .

High-resolution NPD data were recorded at 13 temperatures: 4, 10, 20, 30, 40, 50 60, 70, 100, 150, 200, 250, and 300 K. The NPD data of $T > T_C$ are attributed exclusively to nuclear scattering and can be refined with the space group $P4_12_12$ as shown in Fig. 2(a) and Table I. Single-crystal XRD work suggested a nonstatistical distribution of Si and Ge in monoclinic Gd₅(Si_{1-x}Ge_x)₄ compounds,^{4,17} so we attempted to refine the occupancies of Si and Ge in *t*-Pr₅Si₂Ge₂. For the NPD data at 300 K, the derived Si/Ge

TABLE I. Data of crystallographic structure at selected temperatures for *t*-Pr₅Si₂Ge₂ derived from the fitting to NPD patterns. Space group: $P4_12_12$. M=0.5Si+0.5Ge, *B* is the isotropic temperature factor, and R_P and R_{WP} are residuals of fitting to the pattern and the weighted pattern, respectively. R_B and R_M are Bragg and magnetic *R* factors, respectively. χ^2 is a "goodness of fit" indicator (Ref. 20).

	4 K	40 K	60 K	300 K
a (Å)	7.94849(9)	7.9455(3)	7.9442(2)	7.9667(2)
<i>c</i> (Å)	14.9168(2)	14.9282(6)	14.9395(4)	14.9297(5)
V (Å ³)	942.42(2)	942.42(6)	942.84(4)	947.56(5)
Pr1 (4 <i>a</i>) x	0.3126(4)	0.3132(9)	0.3142(6)	0.3141(9)
B (Å ²)	0.60(3)	0.49(8)	0.60(4)	1.14(6)
Pr2 (8 <i>b</i>) x	0.3670(3)	0.3664(9)	0.3668(5)	0.3657(6)
у	0.0107(3)	0.0109(9)	0.0112(5)	0.0118(7)
Z	0.4545(1)	0.4540(5)	0.4543(2)	0.4552(3)
B (Å ²)	0.54(2)	0.55(5)	0.64(3)	0.87(4)
Pr3 (8b) x	0.1336(3)	0.1334(7)	0.1336(5)	0.1352(7)
У	-0.0145(3)	-0.0138(7)	-0.0145(4)	-0.0136(6)
Ζ	0.8742(3)	0.8749(8)	0.8754(5)	0.8747(6)
B (Å ²)	0.47(2)	0.47(5)	0.51(3)	1.05(4)
M1 (8b) x	0.1993(3)	0.1991(7)	0.1990(4)	0.2003(5)
у	0.1625(3)	0.1617(7)	0.1619(4)	0.1625(5)
Z	0.6929(1)	0.6924(3)	0.6928(2)	0.6920(2)
B (Å ²)	0.51(2)	0.51(5)	0.67(3)	0.88(3)
M2 (8b) x	0.2909(3)	0.2903(8)	0.2911(4)	0.2922(6)
У	0.9314(3)	0.9325(8)	0.9312(4)	0.9329(5)
Z	0.0609(1)	0.0612(3)	0.0608(2)	0.0619(2)
B (Å ²)	0.54(2)	0.60(5)	0.61(3)	0.98(3)
$R_P(\%)/R_{WP}(\%)$	3.68/4.34	8.49/10.0	4.22/5.18	4.19/5.25
$R_B(\%)/R_M(\%)$	4.24/7.37	7.37/14.1	6.15/N	7.61/N
<u>x²</u>	1.36	0.869	0.958	0.904

occupancy ratios are 0.51/0.49 on M1 site with B(M1) $=0.85 \text{ Å}^2$, 0.49/0.51 on M2 site with $B(M2)=1.02 \text{ Å}^2$ when the total Si/Ge ratio was fixed to 1, and 0.46/0.54 on M1 site with $B(M1) = 0.92 \text{ Å}^2$, 0.43/0.57 on M2 site with $B(M2) = 1.12 \text{ Å}^2$ if the total Si/Ge ratio was not fixed. In comparison with the data in Table I, the thermal parameter Bincreases with the Ge occupancy on each site, which could be due to possible correlation between B and occupancy in the refinement. For the m-Pr₅Si₂Ge₂, our previous refinement of powder XRD data at 300 K did not detect any preferential occupation of the Ge and Si atoms,²¹ and the refinement of the present NPD data at 300 K shows similar correlation between B and Ge occupancy as that for the t-Pr₅Si₂Ge₂. Moreover, in contrast to the single-crystal XRD work on Gd₅Si₂Ge₂, the refinement of NPD data shows that in m-Pr₅Si₂Ge₂ the occupancy of Ge atoms is larger than 0.5 on the M1 and M3a sites and smaller than 0.5 on the M2 and

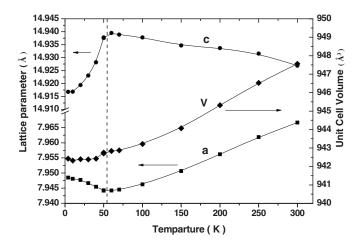


FIG. 4. Temperature dependence of the lattice parameters of t-Pr₅Si₂Ge₂. The vertical dashed line indicates the position of T_C .

*M*3b sites, while the single-crystal XRD work suggested Ge atoms should preferentially occupy both the *M*3a and *M*3b sites.^{4,17} Therefore, we are unable to reach a conclusive result regarding the nonstatistical distribution of the Si and Ge atoms in $Pr_5Si_2Ge_2$ based on the powder diffraction data and will assume a random distribution of the atoms on each site as in many reported powder diffraction works on $R_5(Si_{1-x}Ge_x)_4$ compounds^{10,12,15}

The NPD data of $T < T_C$ comprise scattering contributions of both the nuclear and magnetic lattices. Since the *t*-Pr₅Si₂Ge₂ exhibited appreciable magnetization at 5 K and 50 kOe, possible magnetic structure models should have large ferromagnetic components. A magnetic space group compatible with nonzero total magnetic component should be a ferromagnetic one.²² Other magnetic space groups result in a null resultant spin vector of the atoms on each equivalent site, i.e., an antiferromagentic (AFM) arrangement. There are 275 ferromagnetic space groups among 1651 Shubnikov groups (see Table III in Ref. 22). Thus, if the magnetization curve of a compound exhibits ferromagnetic (FM) or ferrimagnetic (FIM) behavior without a sign of AFM-FM or AFM-FIM metamagnetic transition, the number of possible

TABLE II. Magnetic moment components of Pr atoms in t-Pr₅Si₂Ge₂ at selected temperatures derived from the fitting to NPD data. The atomic positions refer to Table I. Magnetic space group: $P4_12_1'2'$.

	μ_x	μ_y	μ_z	μ
	(μ_B)	(μ_B)	(μ_B)	(μ_B)
		<i>T</i> =4 K		
Pr1	-0.29(3)	0.29(3)	2.75(4)	2.78(4)
Pr2	0.18(5)	-1.86(3)	1.69(3)	2.52(3)
Pr3	0.23(5)	0.01(3)	2.81(3)	2.82(3)
		<i>T</i> =40 K		
Pr1	-0.20(12)	0.20(12)	2.46(12)	2.47(12)
Pr2	0.19(16)	-1.09(10)	1.10(8)	1.56(10)
Pr3	-0.04(20)	-0.03(10)	2.24(7)	2.24(7)

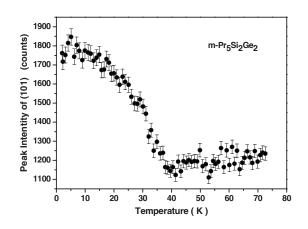


FIG. 5. Temperature dependence of the peak intensity of (101) reflection of m-Pr₅Si₂Ge₂ on warming, measured by high-flux BT-7 spectrometer at NIST-NCNR.

magnetic space group for the compound can be greatly reduced.

There are eight Shubnikov groups derived from $P4_{1}2_{1}2$, i.e., $P4_{1}2_{1}2$, $P4_{1}2_{1}21'$, $P4_{1}'2_{1}2'$, $P4_{1}2_{1}'2'$, $P4_{1}'2_{1}'2$, $P_{c}4_{1}2_{1}2$, $P_{c}4_{1}2_{1}2$, and $P_{l}4_{1}2_{1}2$. The $P4_{1}2_{1}21'$ is nonmagnetic, i.e., a "gray" group. Among the seven magnetic Shubnikov groups, only the $P4_{1}2_{1}'2'$ is ferromagnetic. Therefore, we used the magnetic space group $P4_{1}2_{1}'2'$ to model the magnetic structure of t-Pr₅Si₂Ge₂ below T_{c} . The same magnetic space group was used for the magnetic structure of Nd₅Si₄ by Cadogan *et al.*⁸ For this magnetic structure model, the spin components μ_x and μ_y of the Pr atoms on both the 4a and 8b sites arrange antiferromagnetically along the respective crystal axis, leading to zero net magnetization along the *a* and *b* directions, whereas the spin component μ_z of the Pr atoms arrange ferromagnetically along the *c* axis.

The experimental and calculated NPD patterns of the t-Pr₅Si₂Ge₂ at 4 K is shown in Fig. 2(b). The magnetic structure is depicted in Fig. 3(a), showing the magnetic atoms only. The refinement results of the NPD data at some selected temperatures (4, 40, 60, and 300 K) are listed in Table I and the magnetic moments of the atoms in Table II. The temperature dependence of lattice parameters is shown in Fig. 4. As the temperature decreases, the lattice parameter a and unit cell volume V decrease, while the lattice parameter c increases. At T_C =52 K, c decreases gradually but significantly, and a increases with the further decrease of temperature, indicating a second-order transition. However, a small negative magnetovolume effect is observed, i.e., a decrease of unit cell volume when cooling through the magnetic transition temperature T_C .

B. Crystal and magnetic structures of *m*-Pr₅Si₂Ge₂

NPD experiment at room temperature confirmed that the as-arc-melted sample crystallized in the monoclinic $Gd_5Si_2Ge_2$ -type structure with space group $P112_1/a$. Difference curve of the NPD patterns below and above 40 K signifies the contribution of magnetic scattering at low temperature. The magnetic Bragg peaks can be indexed by the nuclear unit cell. Figure 5 shows the temperature dependence

TABLE III. Data of crystallographic structure at different temperatures for m-Pr₅Si₂Ge₂ derived from the fitting to NPD patterns. Space group: $P112_1/a$. M=0.5Si+0.5Ge, B is the isotropic temperature factor, and R_P and R_{WP} are residuals of fitting to the pattern and the weighted pattern, respectively. R_B and R_M are Bragg and magnetic R factors, respectively. χ^2 is a "goodness of fit" indicator (Ref. 20).

	4 K	30 K	50 K	300 K
a (Å)	7.8105(4)	7.8138(4)	7.8178(4)	7.8232(8)
b (Å)	15.1634(6)	15.1611(7)	15.1596(8)	15.1977(15)
c (Å)	7.9787(4)	7.9778(4)	7.9795(5)	7.9918(7)
γ (deg)	93.867(3)	93.887(3)	93.913(4)	93.798(6)
V (Å)	942.80(7)	942.91(8)	943.48(9)	948.09(16)
$\Pr1(4e) x$	0.328(1)	0.327(1)	0.326(1)	0.326(2)
у	0.2457(5)	0.2452(5)	0.2445(6)	0.2468(9)
z	0.0038(8)	0.0039(9)	0.0064(11)	0.0051(13)
B (Å ²)	0.00	0.03	0.05	0.28(9)
Pr2a (4 <i>e</i>) <i>x</i>	-0.0069(9)	-0.0087(11)	-0.0068(12)	-0.0023(18)
V	0.1002(4)	0.1007(4)	0.0994(6)	0.1013(9)
z	0.1799(9)	0.1816(10)	0.1830(12)	0.1831(17)
B (Å ²)	0.02	0.12	0.20	1.19(11)
Pr2b (4e) x	0.025(1)	0.024(1)	0.021(1)	0.024(2)
у	0.4016(5)	0.3999(6)	0.3986(7)	0.3990(9)
z	0.197(1)	0.193(1)	0.192(1)	0.186(2)
B (Å ²)	0.01	0.10	0.16	0.99(11)
Pr3a (4 <i>e</i>) <i>x</i>	0.358(1)	0.363(1)	0.362(1)	0.359(2)
У	0.8831(4)	0.8837(5)	0.8817(5)	0.8828(8)
z	0.1625(10)	0.1622(10)	0.1619(12)	0.1620(16)
B (Å ²)	0.01	0.08	0.13	0.80(11)
Pr3b (4e) x	0.327(1)	0.327(1)	0.327(1)	0.328(2)
у	0.6217(4)	0.6222(5)	0.6217(6)	0.6228(8)
2	0.1731(9)	0.1702(10)	0.1698(11)	0.1761(16)
B (Å ²)	0.01	0.07	0.12	0.74(10)
M1 (4 <i>e</i>) <i>x</i>	0.2161(9)	0.2176(9)	0.2169(9)	0.213(1)
у	0.2501(5)	0.2511(5)	0.2510(5)	0.2523(6)
2	0.3695(8)	0.3679(8)	0.3688(8)	0.3712(12)
B (Å ²)	0.01	0.09	0.15	0.90(9)
M2 (4 <i>e</i>) x	0.9520(8)	0.9544(8)	0.9532(8)	0.951(1)
у	0.2506(4)	0.2524(4)	0.2527(4)	0.2517(6)
z	0.8992(8)	0.8978(8)	0.8964(8)	0.8960(11)
B (Å ²)	0.01	0.07	0.11	0.66(9)
M3a (4e) x	0.2163(9)	0.2166(9)	0.2158(9)	0.2134(13)
у	0.9560(5)	0.9566(5)	0.9561(4)	0.9560(7)
Z	0.4680(9)	0.4669(9)	0.4669(8)	0.4625(12)
B (Å ²)	0.01	0.07	0.12	0.71(10)
M3b (4e) x	0.1450(8)	0.1455(9)	0.1477(9)	0.1471(13)

	4 K	30 K	50 K	300 K
y	0.5429(4)	0.5440(4)	0.5434(4)	0.5408(6)
Z	0.4689(9)	0.4693(8)	0.4702(8)	0.4736(12)
B (Å ²)	0.01	0.08	0.14	0.81(8)
$R_P(\%)/R_{WP}(\%)$	4.40/5.40	4.24/5.13	4.13/5.04	4.84/5.87
$R_B(\%)/R_M(\%)$	5.60/7.33	6.88/10.1	8.56/N	5.84/N
χ^2	1.94	1.75	1.64	0.822

TABLE III. (Continued.)

of the peak intensity of the (101) reflection on warming, which manifests a magnetic ordering temperature of T_C = 40 K, in good agreement with the magnetization measurement (T_C =38 K).¹⁹ No other magnetic transition occurs below T_C . Magnetization measurement indicated a second-order magnetic transition at T_C .¹⁹

High-resolution NPD data were recorded at four temperatures: 4, 30, 50, and 300 K. The NPD data above T_C can be well fitted by the monoclinic Gd₅Si₂Ge₂-type structure with the space group $P112_1/a$ as shown in Fig. 6(a). The refinement results are listed in Table III. Similar to the discussion on the magnetic structure model of the *t*-Pr₅Si₂Ge₂, the space group $P112_1'/a'$ is the only ferromagnetic space group among the ten Shubnikov groups derived from $P112_1/a$ that is compatible with the appreciable magnetization at 5 K and with the nuclear unit cell of the magnetic structure of m-Pr₅Si₂Ge₂. The same magnetic space group was adopted for monoclinic Nd₅Si_{1,45}Ge_{2,55} and Pr₅Si_{1,5}Ge_{2,5} by Magen et al. based on the representation analysis and the trial-anderror fittings to the NPD data.¹² By the magnetic space group $P112_1'/a'$, all Pr atoms occupy general positions 4e with the spin components arranged ferromagnetically along the *a* and b axes but antiferromagnetically along the c axis. This mag-

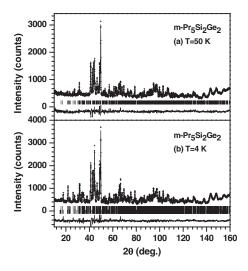


FIG. 6. Experimental (crosses) and calculated (solid line) intensities of m-Pr₅Si₂Ge₂ at (a) 50 K and (b) 4 K. Differences between the experimental and calculated patterns are shown at the bottom of the figure. The vertical bars indicate the expected nuclear reflection positions. The expected magnetic reflection positions are marked by the bars on the lower row in (b).

netic structure model gives a satisfactory fitting to the NPD data below T_C as shown in Fig. 6(b).

Primary refinements of the crystal and magnetic structures of *m*-Pr₅Si₂Ge₂ were carried out with 70 fitted parameters, about twice of the fitted parameters for the *t*-Pr₅Si₂Ge₂ (43). Though the refinements converged satisfactorily and the derived crystallographic and magnetic data were close to those of the reported Nd₅Si_{1.45}Ge_{2.55} and Pr₅Si_{1.5}Ge_{2.5},¹² the fitted thermal parameters *B* on some sites did not follow the general decreasing trend with the decrease of temperature due to possible correlation among the fitted parameters. Therefore, we fixed the thermal parameters on each site as $B_i(T)$ = $B_i(300 \text{ K})T/300$ during the refinements, where $B_i(300)$ is the thermal parameter on site *i* at 300 K and is derived from the refinement to the NPD data at 300 K (crystallographic structure only with 35 fitted parameters).

The magnetic structure of the m-Pr₅Si₂Ge₂ is depicted in Fig. 3(b), showing the magnetic atoms only. The refinement results of the NPD data are listed in Table III and the magnetic moments of the atoms in Table IV. The temperature dependence of lattice parameters is shown in Fig. 7. Though there is not enough data around T_C , a small negative magnetovolume effect is discernable.

TABLE IV. Magnetic moment components of Pr atoms in m-Pr₅Si₂Ge₂ at selected temperatures derived from the fitting to NPD data. The atomic positions refer to Table III. Magnetic space group: $P112_1'/a'$.

	μ_x	μ_y	μ_z	μ
	(μ_B)	(μ_B)	(μ_B)	(μ_B)
		<i>T</i> =4 K		
Pr1	2.24(5)	0.05(9)	-0.29(8)	2.26(5)
Pr2a	3.03(8)	-0.29(9)	0.27(8)	3.07(9)
Pr2b	1.28(7)	1.94(9)	-0.19(8)	2.26(9)
Pr3a	1.92(6)	0.76(9)	0.34(9)	2.04(6)
Pr3b	2.50(7)	-0.52(9)	1.38(9)	2.93(7)
		<i>T</i> =30 K		
Pr1	1.80(7)	-0.04(15)	-0.25(11)	1.82(7)
Pr2a	2.25(10)	-0.27(14)	-0.04(11)	2.28(11)
Pr2b	0.86(9)	1.12(16)	-0.04(10)	1.36(15)
Pr3a	1.24(7)	0.46(15)	0.52(13)	1.39(9)
Pr3b	1.71(9)	0.07(16)	0.84(15)	1.90(10)

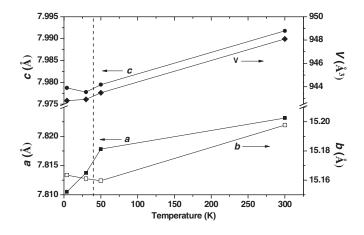


FIG. 7. Temperature dependence of the lattice parameters of m-Pr₅Si₂Ge₂. The vertical dashed line indicates the position of T_C .

IV. DISCUSSION

The crystal structures of m-Pr₅Si₂Ge₂ and t-Pr₅Si₂Ge₂ are depicted in Figs. 8(a) and 9(a), respectively. They have many similarities: (i) all Pr atoms have six M atoms (=0.5Si +0.5Ge) as the nearest neighbors with a bond distance of $d_{\text{Pr-M}} \sim 3.1$ Å; (ii) Pr atoms have 8–10 neighboring Pr atoms within the $d_{\text{Pr-Pr}}$ range <4.35 Å; (iii) Pr1 at 4e sites in m-Pr₅Si₂Ge₂ and at 4a sites in t-Pr₅Si₂Ge₂ have eight neighboring Pr atoms, with $d_{\text{Pr-Pr}} \sim 3.6$ Å. The eight Pr atoms form a slightly distorted cube and the six M atoms form a slightly distorted cube and the six M atoms form a slightly distorted octahedron, which acts as the building unit [Pr M_6]Pr₈ of both the structures as we describe below, and (iv) other Pr atoms with much shorter $d_{\text{Pr-Pr}} (\sim 3.6$ Å) than the distances to the additional 6–8 neighboring Pr atoms (~3.9 Å).

The difference between the two structures is also salient, however. In the t-Pr₅Si₂Ge₂, all M atoms are covalently

bonded with $d_{M-M} \sim 2.6$ Å, while only 3/4 of the *M* atoms in the m-Pr₅Si₂Ge₂ form covalent bonds (M1-M2 and M3b-M3b bonds, $d_{M-M} \sim 2.6$ Å). The most striking difference between the two structures is the way the building unit $[\Pr M_6]\Pr_8$ connect with each other. In *m*- $\Pr_5Si_2Ge_2$, the building units share four nonadjacent and parallel edges of a Pr_8 cube, forming an infinitive two-dimensional $\frac{2}{\infty} [Pr_5 M_4]$ slab parallel to the *ac* plane [Figs. 8(a) and 8(b)]. Half of the adjacent slabs are connected by covalent M-M bonds (M3b-M3b bonds). In *t*-Pr₅Si₂Ge₂, the building units also share four nonadjacent but *perpendicular* edges of a Pr₈ cube, forming a cockle-stair-like stacking of the cubes [Figs. 9(a) and 9(b)]. In addition, each M1-M2 bond connects to three Pr_8 cubes in *t*-Pr₅Si₂Ge₂, while in *m*-Pr₅Si₂Ge₂, each M1-M2 bond connects to four Pr_8 cubes and each M3b-M3b bond to two Pr_8 cubes. These similarities and differences between the structures of m- and t-Pr₅Si₂Ge₂ should be responsible for their relatively stable existence at room temperature, i.e., the difference in free energy between these two structures is very small, and for the structuredependent physical properties.

Below T_C , both the compounds exhibit noncollinear magnetic structures. For *m*-Pr₅Si₂Ge₂, the net magnetic components exist along the a and b directions. The ferromagnetic components occur mainly along the *a* direction for the Pr atoms except for Pr2b [Fig. 3(b)]. For Pr2b, the magnetic components along a and b directions are comparable. At 4 K, the magnetic moments of Pr2a and Pr3b are close to the saturation moment of a free Pr^{3+} ion $(3.5\mu_B)$, while the moments of other Pr atoms are a little smaller because of the CEF effects that partially quench the orbital angular moment. The average moment of Pr atom at 4 K is $2.51 \mu_B$. The average net moment on the *ab* plane is $2.21 \mu_B$ per Pr atom, in reasonable agreement with the magnetization at 5 K and 50 kOe (1.72 μ_B per Pr atom),¹⁹ since the magnetization curve (M-H) records exclusively the projection of ferromagnetic component in magnetic domains along the applied field

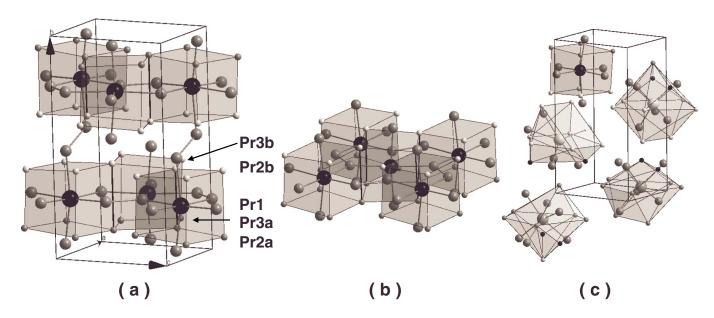


FIG. 8. (Color online) (a) Crystal structure of m-Pr₅Si₂Ge₂, (b) the connection of five building units [Pr M_6]Pr₈, and (c) the Prcoordination polyhedrons of Pr atoms. The size of the coordinating Pr atoms on the vertices of the polyhedrons is reduced by 60%.

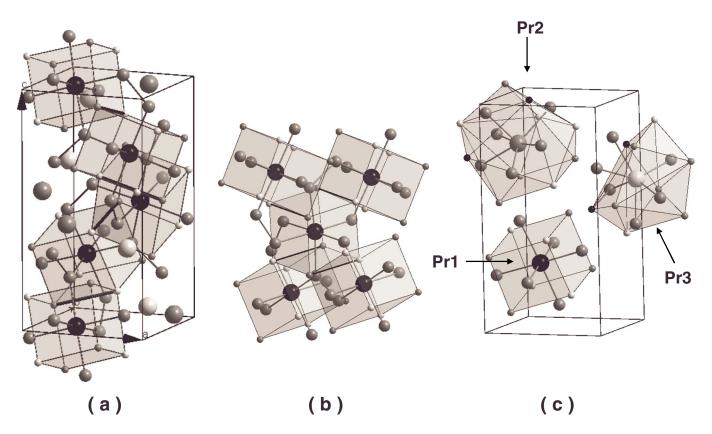


FIG. 9. (Color online) (a) Crystal structure of t-Pr₅Si₂Ge₂, (b) the connection of five building units [Pr M_6]Pr₈, and (c) the Pr-coordination polyhedrons of Pr atoms. The size of the coordinating Pr atoms on the vertices of the polyhedrons is reduced by 60%.

direction for a stable noncollinear magnetic structure.

For *t*-Pr₅Si₂Ge₂, net magnetic moment occurs exclusively along the c direction. Figure 10 shows the temperature dependence of magnetic moment components of Pr atoms on each site. The magnetic ordering of Pr atoms develops simultaneously on different sites, in contrast to Pr₅Ge₄, in which magnetic ordering of Pr atoms on different sites took place at different temperatures.⁹ From Fig. 10, it can be seen that the moments of Pr1 and Pr3 align almost along the c axis, whereas the moment of Pr2 lies almost on the bc plane with comparable b and c components. At 4 K, the average moment of Pr is $2.69\mu_B$, a little smaller than the saturation moment of a free Pr^{3+} ion $(3.5\mu_B)$, possible due to the presence of the CEF effects. The average net moment along the caxis is $2.35\mu_B$ per Pr atom, which is appreciably larger than the magnetization at 5 K and 50 kOe $(1.33\mu_B \text{ per Pr atom})$.¹⁹ The smaller observed magnetization can be attributed to an unsaturation state of the compound in the experiments. The field dependence of magnetization showed that it was more difficult for the t-Pr₅Si₂Ge₂ to approach the saturation than the m-Pr₅Si₂Ge₂, which could probably be associated with a larger magnetocrystalline anisotropy or with the domain-wall pinning effects due to the defects formed during quenching to water from high temperature.

It is well known that in metallic rare earth and rare-earthrich intermetallic compounds, the Ruderman-Kittel-Kasuya-Yosida (RKKY) interaction between R atoms plays an important role. The RKKY interaction is a long-range indirect exchange interaction and is sensitive to the distance between the *R* atoms and their chemical environments. The RKKY interaction model is likely applicable to the $R_5(Si_xGe_{1-x})_4$ compounds.⁴ The Pr-coordination polyhedrons of Pr atoms in the structures of *m*- and *t*-Pr₅Si₂Ge₂ are shown in Figs. 8(c) and 9(c), respectively. The chemical environments around Pr atoms on different sites are remarkably different. The Pr-Pr distance varies in the range of 3.5–4.2 Å. Therefore, both AFM and FM exchange interactions between Pr atoms could exist in the compound. The competition between the AFM

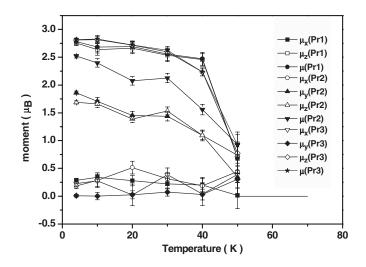


FIG. 10. Temperature dependence of magnetic moments of Pr atoms in t-Pr₅Si₂Ge₂.

and FM interactions and different magnetocrystalline anisotropies on different sites should be the reason for the occurrence of the complex noncollinear magnetic structures.

Our refinement results of the magnetic structures of t- and m-Pr₅Si₂Ge₂ are basically similar to those of Nd₅Si₄,⁸ Pr₅Si_{1.5}Ge_{2.5}, and Nd₅Si_{1.45}Ge_{2.55},¹² especially regarding the easy magnetization direction (EMD). For rare earth intermetallic compounds, the EMD is essentially determined by the chemical environment around the R atoms and the shape of the 4*f*-electron distribution characterized by the second-order Stevens coefficient α_J . In orthorhombic and monoclinic $R_5(\text{Si}_{1-x}\text{Ge}_x)_4$ (x ~ 0.5), the chemical environments around R atoms are similar, and the available magnetic structural data show that the EMD of the monoclinic phase is along the aaxis for $\alpha_I < 0$ [R=Tb,^{10,11} Pr, Nd (Ref. 12)] and along the b axis for $\alpha_J > 0$ [R=Er (Ref. 15)]. In addition, while the dramatic magnetovolume effect in $R_5(Si_{1-x}Ge_x)_4$ for R=Gd and Tb can be attributed to the simultaneous occurrence of the first-order magnetic and martensiticlike structural phase transitions,^{3,5,11} small negative magnetovolume effect is observed in *m*- and *t*-Pr₅Si₂Ge₂ around T_C as shown in Figs. 4 and 7, in contrast to the small positive magnetovolume effect in $Er_5(Si_{1-x}Ge_x)_4$. For these three latter compounds, no structural phase transition takes place around T_{C} . In general, the magnetovolume effect can result from a competition between magnetic energy and elastic energy. A negative magnetovolume effect might indicate an increased resultant exchange interaction as the distance between magnetic atoms decreases. Figures 4 and 7 show that the largest change of the lattice constant occurs always along the EMD for t- and *m*-Pr₅Si₂Ge₂ compounds.

V. SUMMARY

The tetragonal t-Pr₅Si₂Ge₂ crystallizes in the Zr₅Si₄-type structure with the space group $P4_12_12$ down to 4 K. Long-range magnetic ordering takes place at T_C =52 K, and the magnetic structure can be modeled with the magnetic space group $P4_12_1'2'$. The magnetic structure shows a net ferro-

magnetic component exclusively along the *c* axis. No other magnetic transition is manifested below T_c . The lattice parameter *a* and unit cell volume *V* decrease with the decrease of temperature, while the lattice parameter *c* increases. Below $T_c=52$ K, *c* decreases significantly and *a* increases gradually with the further decrease of temperature, indicating a second-order magnetic transition. Refinements of the temperature-dependent NPD data reveal that the magnetic ordering of the Pr atoms develops simultaneously on different sites.

The monoclinic *m*-Pr₅Si₂Ge₂ crystallizes in the Gd₅Si₂Ge₂-type structure with the space group $P112_1/a$ down to 4 K. Long-range magnetic ordering occurs at T_C = 40 K, and the magnetic structure can be modeled with the magnetic space group $P112_1'/a'$, exhibiting net ferromagnetic components along the *a* and *b* directions. No other magnetic transition is observed below T_C .

For both the compounds, a small negative magnetovolume effect, i.e., a decrease of unit cell volume when cooling through the magnetic transition temperature T_C , is observed. The largest change of the lattice constant occurs always along the EMD of compounds. In the scenario of the RKKY interaction model, the competition between the AFM and FM interactions coexisting in the compounds and the different magnetocrystalline anisotropies on different Pr sites should be the reason for the occurrence of the complex noncollinear magnetic structures of the *t*- and *m*-Pr₅Si₂Ge₂.

The crystallographic structures of m-Pr₅Si₂Ge₂ and t-Pr₅Si₂Ge₂ have similarities and differences in many aspects, which should be responsible for their relatively stable existence at room temperature and the structure-dependent physical properties of the polymorphic Pr₅Si₂Ge₂.

ACKNOWLEDGMENTS

The work was supported by the National Natural Science Foundation of China under Grants No. 50025102 and No. 50631040, the State Key Project of Fundamental Research under Grant No. 2006CB601101, and the exchange program between NIST and the Chinese Academy of Sciences.

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